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**Abstract of the Disclosure**

In a semiconductor laser device, an AlGaN buffer layer, a GaN layer, an n-GaN layer, an n-AlGaN cladding layer, an MQW light emitting layer, a p-AlGaN cladding layer, a 5 p-first GaN cap layer, a current blocking layer composed of n-AlGaN, and a p-second GaN cap layer are stacked in this order on a sapphire substrate, and a ridge portion having an upper surface having a width  $W_1$  is formed by etching. The current blocking layer has an opening having a width  $W_2$  on 10 the upper surface of the ridge portion. The width  $W_2$  of the opening is smaller than the width  $W_1$  of the upper surface of the ridge portion. Accordingly, in a light emitting region of the MQW light emitting layer, a saturable light absorbing region is formed on both sides of a current injection region.